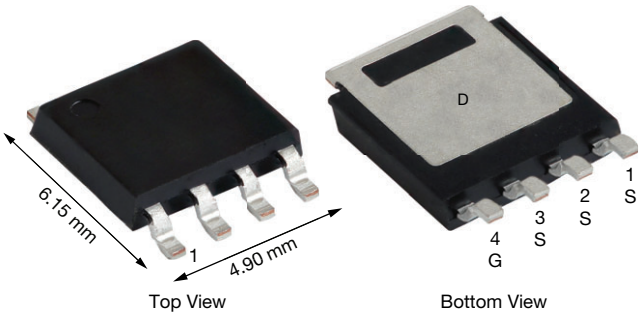
# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

**PowerPAK® SO-8L**




Top View

Bottom View

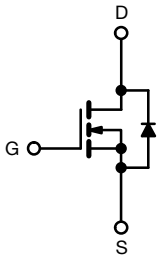
## FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % $R_g$ and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE




N-Channel MOSFET

| PRODUCT SUMMARY | |
|---|---|
| $V_{DS}$ (V) | 60 |
| $R_{DS(on)}$ (Ω) at $V_{GS}$ = 10 V | 0.0029 |
| $I_D$ (A) | 293 |
| Configuration | Single |
| Package | PowerPAK SO-8L |

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|
| Drain-source voltage | | $V_{DS}$ | 60 | V |
| Gate-source voltage | | $V_{GS}$ | ± 20 | |
| Continuous drain current | $T_C$ = 25 °C [a] | $I_D$ | 293 | A |
| | $T_C$ = 125 °C | | 169 | |
| Continuous source current (diode conduction) [a] | | $I_S$ | 454 | |
| Pulsed drain current [b] | | $I_{DM}$ | 335 | |
| Single pulse avalanche current | L = 0.1 mH | $I_{AS}$ | 52 | |
| Single pulse avalanche energy | | $E_{AS}$ | 135 | mJ |
| Maximum power dissipation | $T_C$ = 25 °C | $P_D$ | 500 | W |
| | $T_C$ = 125 °C | | 166 | |
| Operating junction and storage temperature range | | $T_J$, $T_{stg}$ | -55 to +175 | °C |
| Soldering recommendations (peak temperature) [d] | | | 260 | |

**THERMAL RESISTANCE RATINGS**

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|
| Junction-to-ambient | PCB mount [c] | $R_{thJA}$ | 42 | °C/W |
| Junction-to-case (drain) | | $R_{thJC}$ | 0.30 | |

**Notes**

a. Package limited
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
c. When mounted on 1" square PCB (FR4 material)
d. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

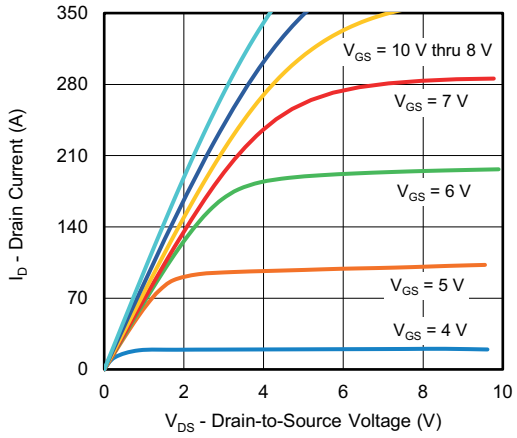
| **SPECIFICATIONS** ($T_C$ = 25 °C, unless otherwise noted) | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Drain-source breakdown voltage | $V_{DS}$ | $V_{GS}$ = 0, $I_D$ = 250 µA | | 60 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | | 2.5 | 3.0 | 3.5 | |
| Gate-source leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | - | - | ± 100 | nA |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V | - | - | 1 | µA |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V, $T_J$ = 125 °C | - | - | 50 | |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V, $T_J$ = 175 °C | - | - | 250 | |
| On-state drain current [a] | $I_{D(on)}$ | $V_{GS}$ = 10 V | $V_{DS}$ ≥ 5 V | 30 | - | - | A |
| Drain-source on-state resistance [a] | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 15 A | - | 0.00235 | 0.0029 | Ω |
| | | $V_{GS}$ = 10 V | $I_D$ = 15 A, $T_J$ = 125 °C | - | - | 0.0049 | |
| | | $V_{GS}$ = 10 V | $I_D$ = 15 A, $T_J$ = 175 °C | - | - | 0.0060 | |
| Forward transconductance [b] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 10 A | | - | 23 | - | S |
| **Dynamic [b]** | | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{GS}$ = 0 V | $V_{DS}$ = 25 V, f = 1 MHz | - | 4365 | 6111 | pF |
| Output capacitance | $C_{oss}$ | | | - | 1828 | 2560 | |
| Reverse transfer capacitance | $C_{rss}$ | | | - | 53 | 75 | |
| Total gate charge [c] | $Q_g$ | $V_{GS}$ = 10 V | $V_{DS}$ = 30 V, $I_D$ = 40 A | - | 54 | 81 | nC |
| Gate-source charge [c] | $Q_{gs}$ | | | - | 21 | - | |
| Gate-drain charge [c] | $Q_{gd}$ | | | - | 4 | - | |
| Gate resistance | $R_g$ | f = 1 MHz | | 0.6 | 1.3 | 2.0 | Ω |
| Turn-on delay time [c] | $t_{d(on)}$ | $V_{DD}$ = 30 V, $R_L$ = 0.75 Ω<br>$I_D$ ≅ 40 A, $V_{GEN}$ = 10 V, $R_g$ = 1 Ω | | - | 17 | 26 | ns |
| Rise time [c] | $t_r$ | | | - | 5 | 9 | |
| Turn-off delay time [c] | $t_{d(off)}$ | | | - | 29 | 44 | |
| Fall time [c] | $t_f$ | | | - | 4 | 8 | |
| **Source-Drain Diode Ratings and Characteristics [b]** | | | | | | | |
| Pulsed current [a] | $I_{SM}$ | | | - | - | 335 | A |
| Forward voltage | $V_{SD}$ | $I_F$ = 15 A, $V_{GS}$ = 0 V | | - | - | 1.1 | V |
| Body diode reverse recovery time | $t_{rr}$ | $I_F$ = 8 A, di/dt = 100 A/µs | | - | 50 | 100 | ns |
| Body diode reverse recovery charge | $Q_{rr}$ | | | - | 52 | 104 | nC |
| Reverse recovery fall time | $t_a$ | | | - | 22 | - | ns |
| Reverse recovery rise time | $t_b$ | | | - | 29 | - | |
| Body diode peak reverse recovery current | $I_{RM(REC)}$ | | | - | 1.8 | - | A |

**Notes**

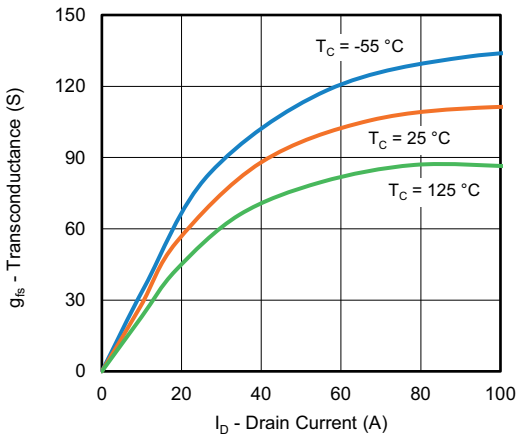
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

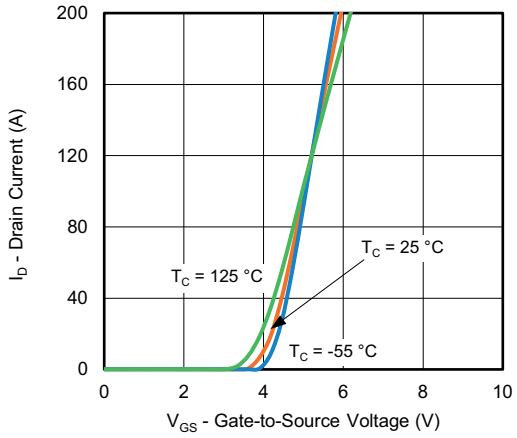
## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)



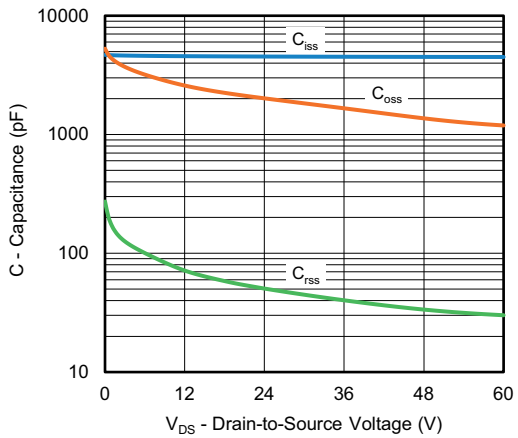

**Output Characteristics**



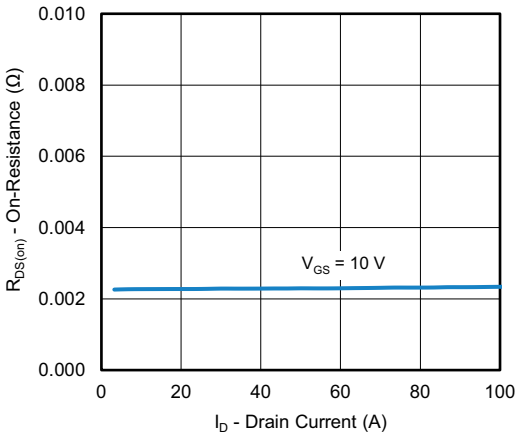

**Transconductance**



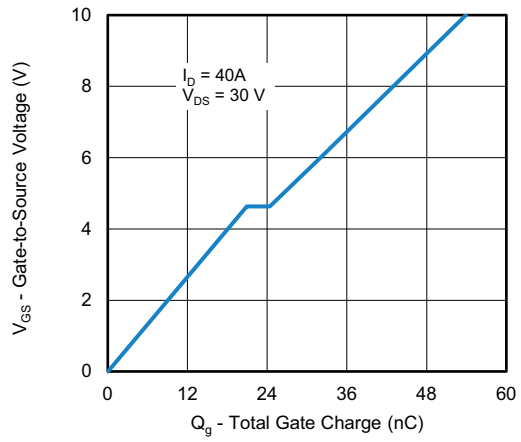

**Transfer Characteristics**




**Capacitance**

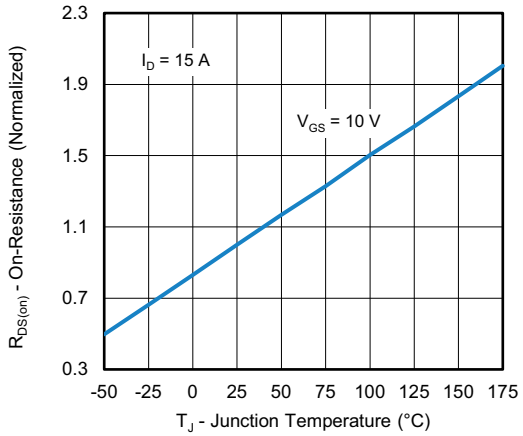



**On-Resistance vs. Drain Current**

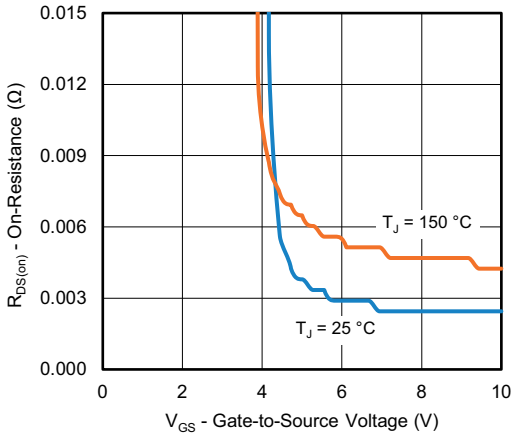



**Gate Charge**

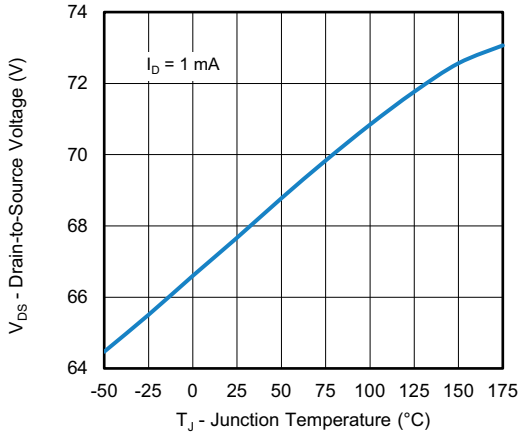
## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)



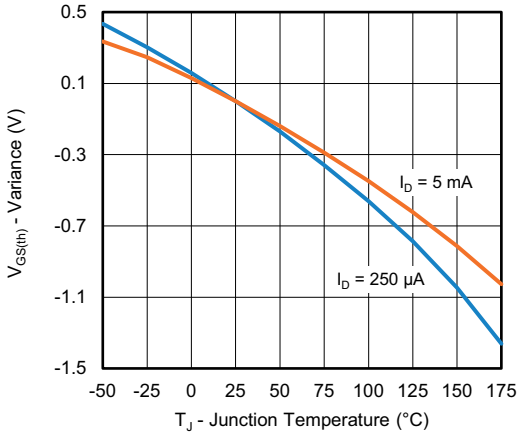

**On-Resistance vs. Junction Temperature**



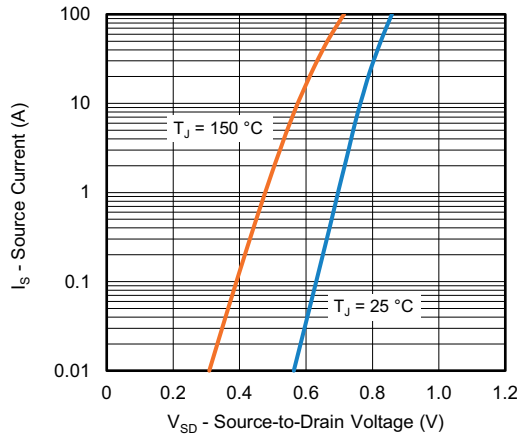

**On-Resistance vs. Gate-to Source Voltage**



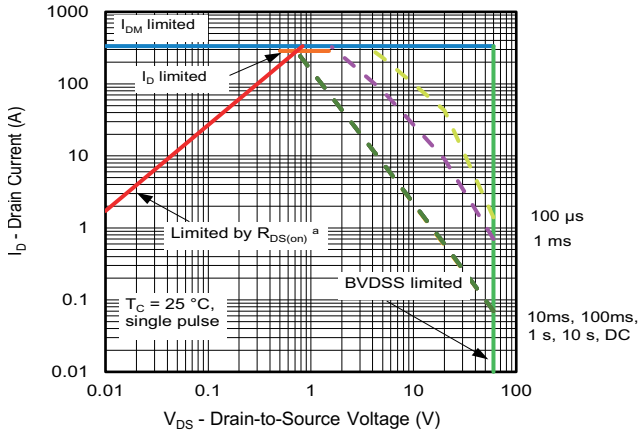

**Drain Source Breakdown vs. Junction Temperature**




**Threshold Voltage**




**Source Drain Diode Forward Voltage**

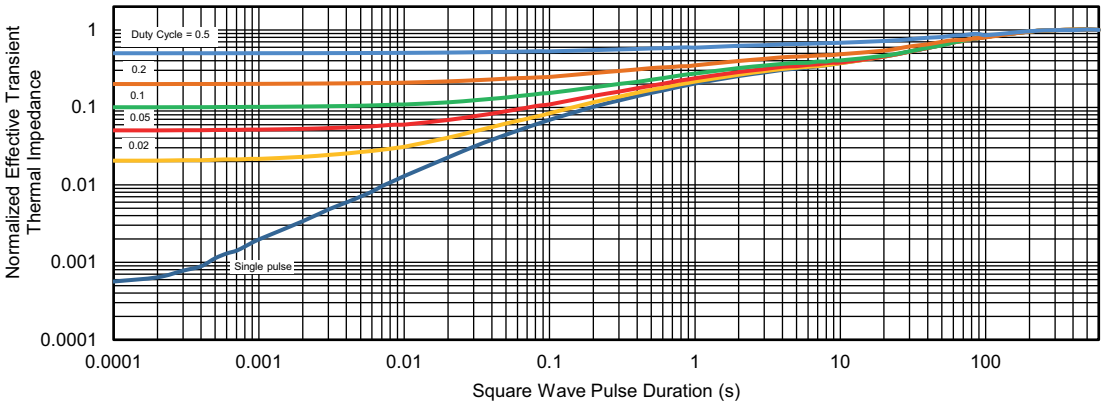



**Safe Operating Area**

**Note**

a. $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified

**TYPICAL CHARACTERISTICS** ($T_A$ = 25 °C, unless otherwise noted)




**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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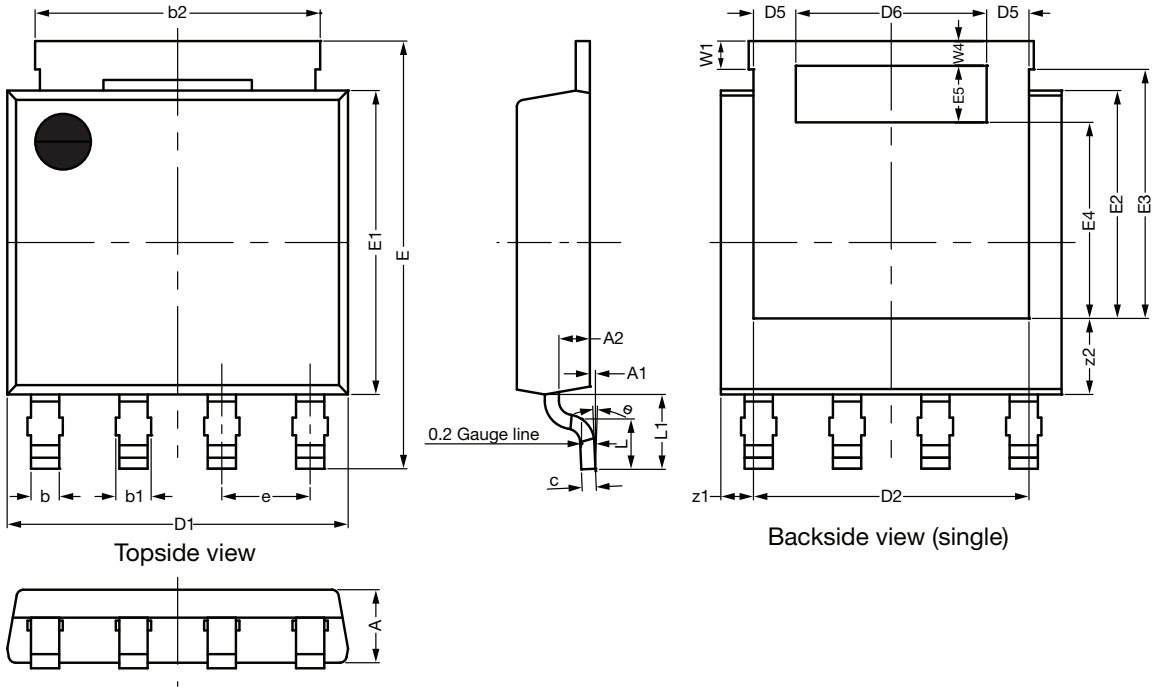
# PowerPAK® SO-8L Case Outline 3




Topside view

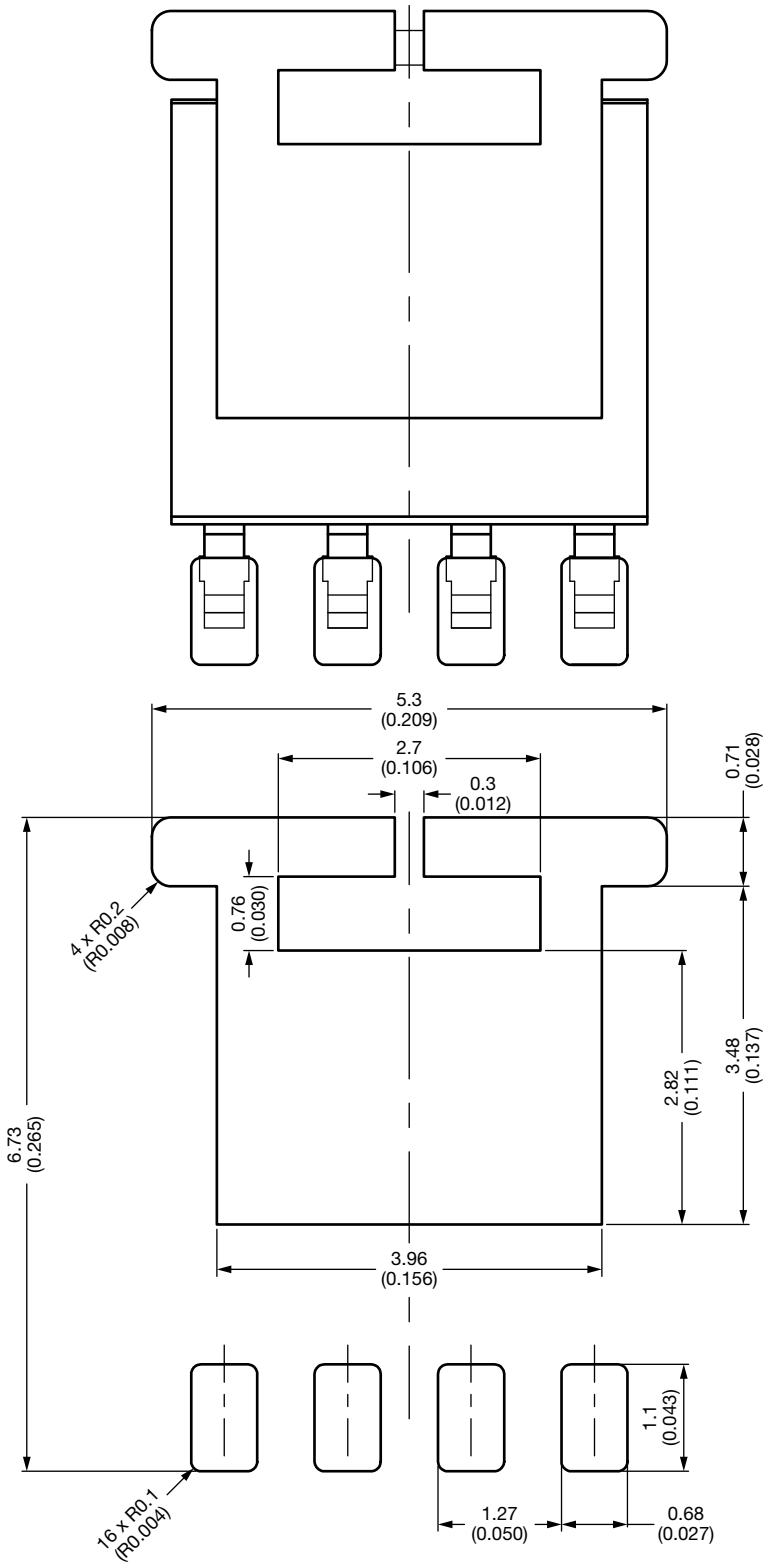
Backside view (single)

| DIM. | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 1.00 | 1.05 | 1.10 | 0.039 | 0.041 | 0.043 |
| A1 | 0.00 | --- | 0.127 | 0.000 | --- | 0.005 |
| A2 | 0.40 | 0.45 | 0.50 | 0.016 | 0.018 | 0.020 |
| b | 0.33 | 0.41 | 0.49 | 0.013 | 0.016 | 0.019 |
| b1 | 0.43 | 0.51 | 0.59 | 0.017 | 0.020 | 0.023 |
| b2 | 4.00 | 4.10 | 4.20 | 0.157 | 0.161 | 0.165 |
| c | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 |
| D2 | 3.86 | 3.96 | 4.06 | 0.152 | 0.156 | 0.160 |
| D5 | 0.51 | 0.61 | 0.71 | 0.020 | 0.024 | 0.028 |
| D6 | 2.64 | 2.74 | 2.84 | 0.104 | 0.108 | 0.112 |
| e | | 1.27 BSC | | | 0.050 BSC | |
| E | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 |
| E1 | 4.27 | 4.37 | 4.47 | 0.168 | 0.172 | 0.176 |
| E2 | 3.18 | 3.28 | 3.38 | 0.125 | 0.129 | 0.133 |
| E3 | 3.48 | 3.58 | 3.68 | 0.137 | 0.141 | 0.145 |
| E4 | 2.72 | 2.82 | 2.92 | 0.107 | 0.111 | 0.115 |
| E5 | 0.71 | 0.81 | 0.91 | 0.028 | 0.032 | 0.036 |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 |
| W1 | 0.31 | 0.41 | 0.51 | 0.012 | 0.016 | 0.020 |
| W4 | 0.31 | 0.36 | 0.41 | 0.012 | 0.014 | 0.016 |
| z1 | 0.37 | 0.47 | 0.57 | 0.015 | 0.019 | 0.022 |
| z2 | 0.99 | 1.09 | 1.19 | 0.039 | 0.043 | 0.047 |
| θ | 0° | --- | 5° | 0° | --- | 5° |
| ECN: S19-0643-Rev. B, 05-Aug-2019<br>DWG: 6067 | | | | | | |

**Note**

- Millimeter will govern

# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear




Dimensions in Millimeters (Inches)

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